

UP0487C

Silicon N-channel MOSFET

For switching circuits

■ Features

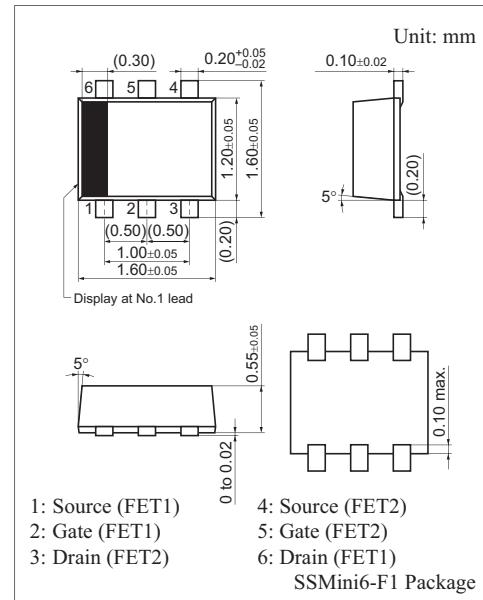
- High-speed switching
- Incorporating a built-in gate protection-diode
- Two elements incorporated into one package (Each transistor is separated)
- SSMini type package, reduction of the mounting area and assembly cost

■ Basic Part Number

- 2SK3937 \times 2

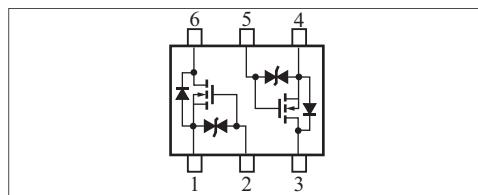
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	20	V
Gate-source surrender voltage	V_{GSS}	± 12	V
Drain current	I_D	100	mA
Peak drain current	I_{DP}	200	mA
Total power dissipation	P_T	125	mW
Channel temperature	T_{ch}	125	°C
Storage temperature	T_{stg}	-55 to +125	°C



Marking Symbol: 2V

Internal Connection

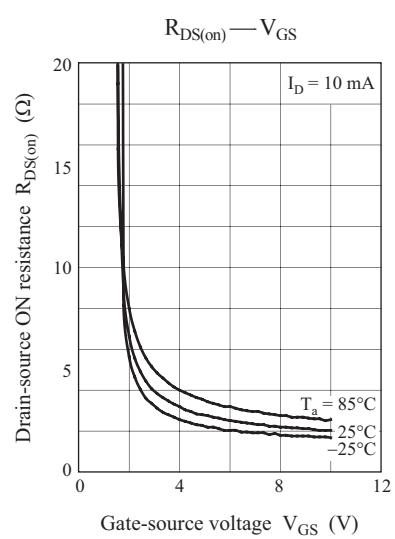
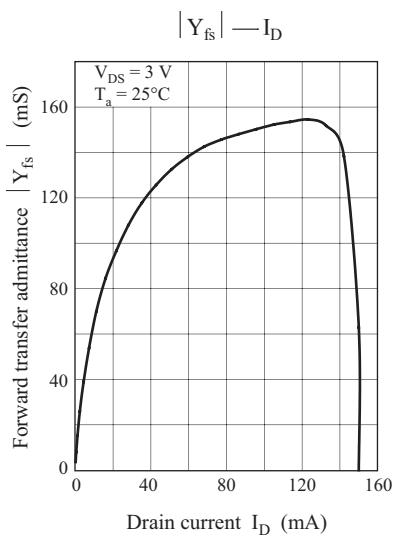
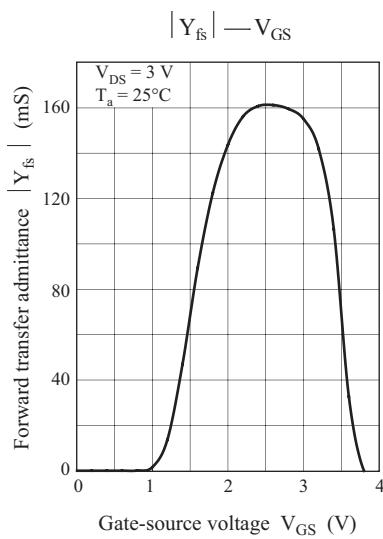
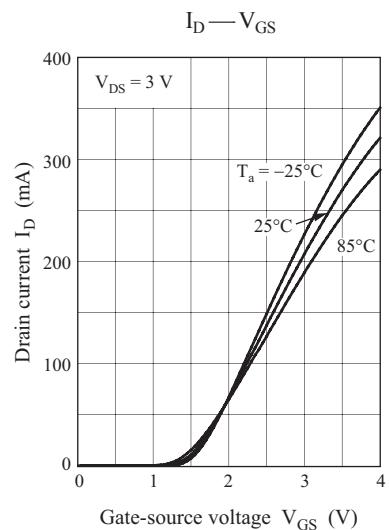
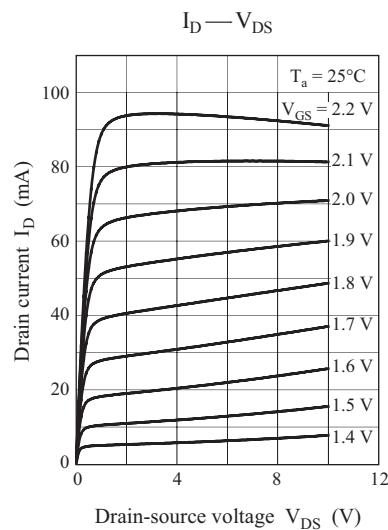
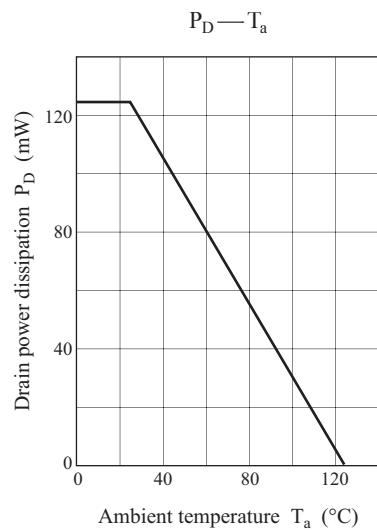
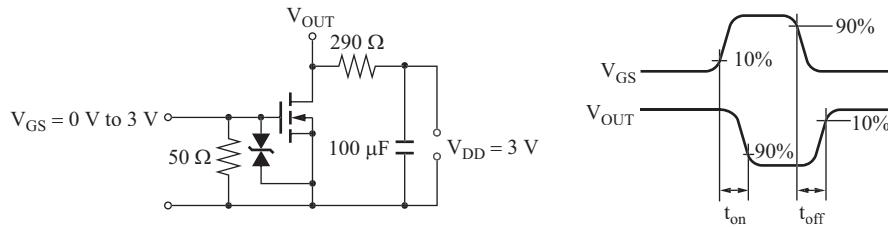


■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 10 \mu A, V_{GS} = 0$	20			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 10 V, V_{GS} = 0$			1.0	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 10 V, V_{DS} = 0$			± 10	μA
Gate threshold voltage	V_{TH}	$I_D = 50 \mu A, V_{DS} = 5.0 V$	0.4		1.3	V
Drain-source ON resistance	$R_{DS(on)}$	$I_D = 1 mA, V_{GS} = 1.8 V$		6	13	Ω
		$I_D = 10 mA, V_{GS} = 2.5 V$		4	6	
		$I_D = 10 mA, V_{GS} = 4.0 V$		3	4	
Forward transfer admittance	$ Y_{fs} $	$I_D = 10 mA, V_{DS} = 3 V,$	20	55		mS
Short-circuit input capacitance (Common source)	C_{iss}	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$			10	pF
Short-circuit output capacitance (Common source)	C_{oss}				13	
Reverse transfer capacitance (Common source)	C_{rss}				5	
Turn-on time *	t_{on}	$V_{DD} = 3 V, V_{GS} = 0 V \text{ to } 3 V, I_D = 10 mA$		250		ns
Turn-off time *	t_{off}	$V_{DD} = 3 V, V_{GS} = 3 V \text{ to } 0 V, I_D = 10 mA$		480		ns

■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. * : t_{on} , t_{off} measurement circuit

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